

Silicon PNP Power Transistors

2SB827

DESCRIPTION

- With TO-3PN package
- Complement to type 2SD1063
- Wide area of safe operation
- Low collector-emitter saturation voltage :  
 $V_{CE(sat)} = (-)0.4V$  max.

APPLICATIONS

- Universal high current switching as solenoid driving, high speed inverter and converter.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

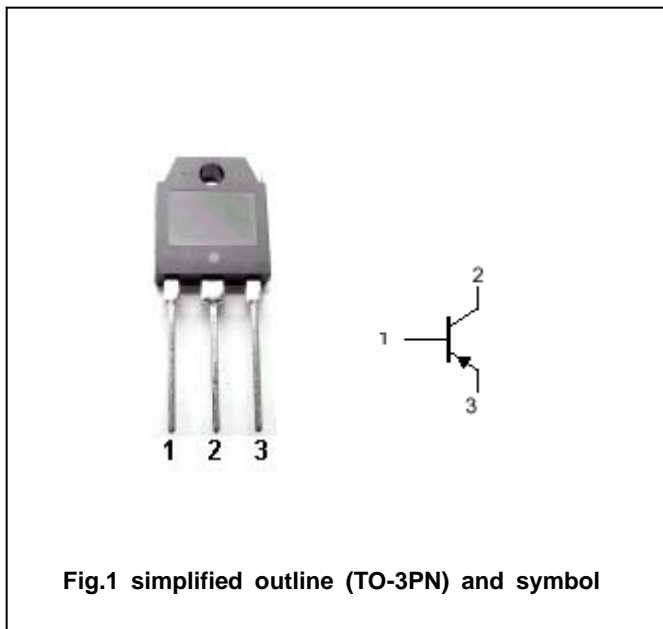


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-60	V
$V_{CEO}$	Collector-emitter voltage	Open base	-50	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current (DC)		-7	A
$I_{CP}$	Collector current (Pulse)		-14	A
$P_C$	Collector power dissipation	$T_C=25$	60	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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**CHARACTERISTICS**

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -1\text{mA}; R_{BE} = \infty$	-50			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1\text{mA}; I_E = 0$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -1\text{mA}; I_C = 0$	-6			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = -4\text{A}; I_B = -0.4\text{A}$			-0.4	V
$I_{CBO}$	Collector cut-off current	$V_{CB} = -40\text{V}; I_E = 0$			-0.1	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	mA
$h_{FE-1}$	DC current gain	$I_C = -1\text{A}; V_{CE} = -2\text{V}$	70		280	
$h_{FE-2}$	DC current gain	$I_C = -5\text{A}; V_{CE} = -2\text{V}$	30			
$f_T$	Transition frequency	$I_C = -1\text{A}; V_{CE} = -5\text{V}$		10		MHz

Switching times

$t_{on}$	Turn-on time	$I_C = -2.0\text{A}; I_{B1} = -I_{B2} = -0.2\text{A}$ $V_{CC} = -20\text{V}; R_L = 10$		0.20		$\mu\text{s}$
$t_{stg}$	Storage time			0.70		$\mu\text{s}$
$t_f$	Fall time			0.10		$\mu\text{s}$

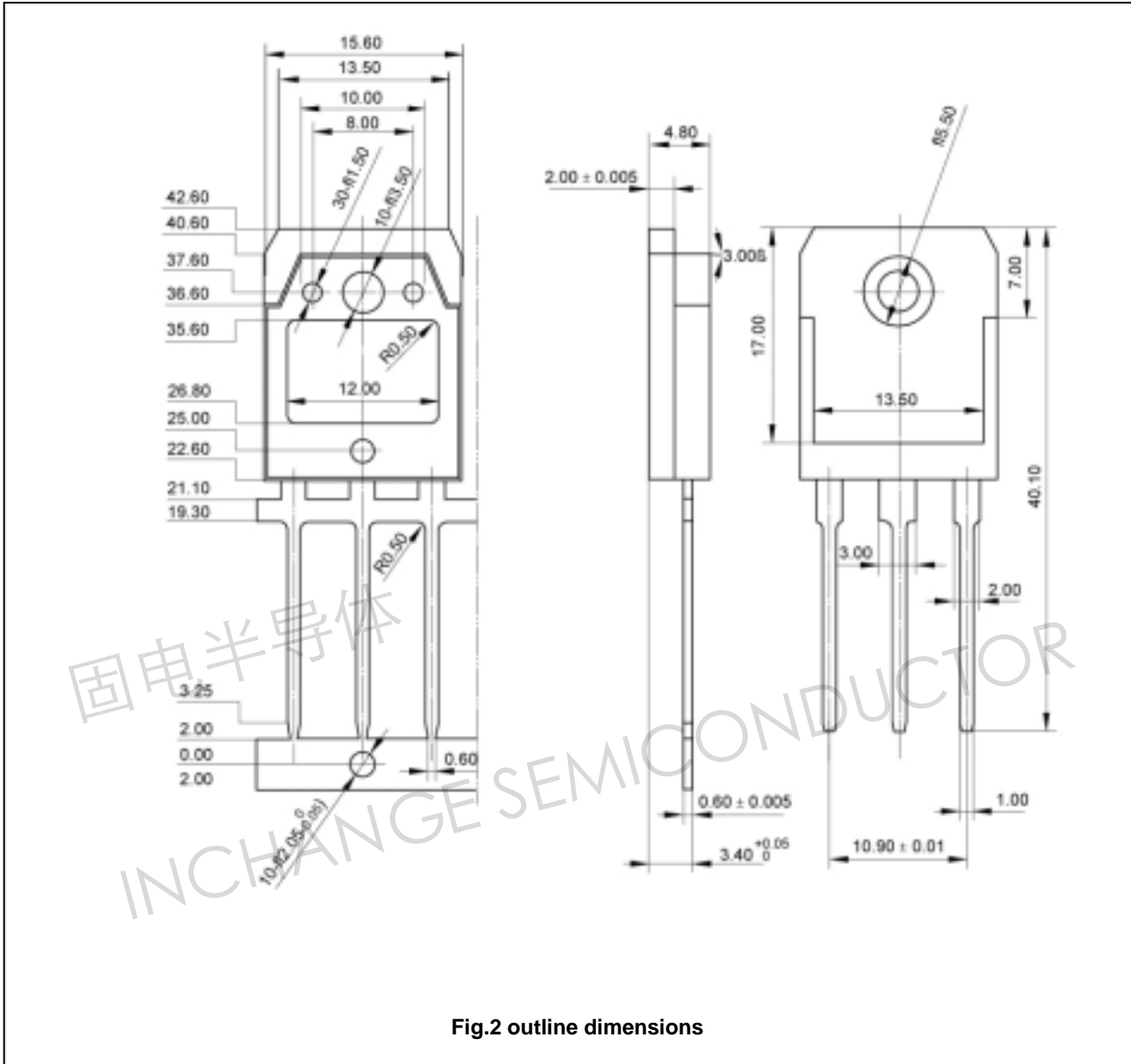
◆  **$h_{FE-1}$  Classifications**

Q	R	S
70-140	100-200	140-280

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PACKAGE OUTLINE



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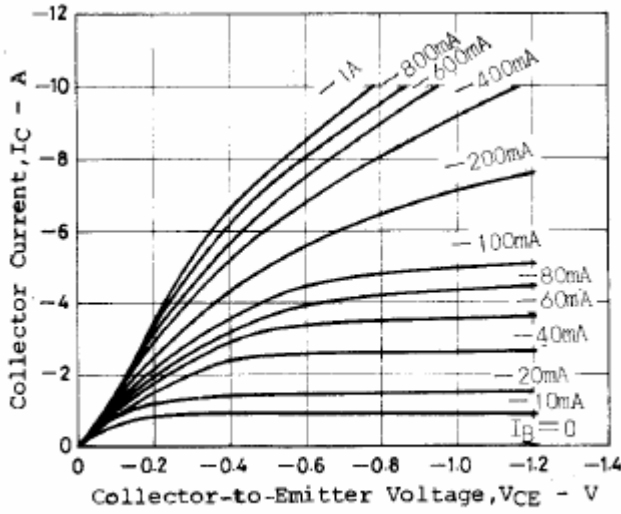


Fig.3 Static Characteristic

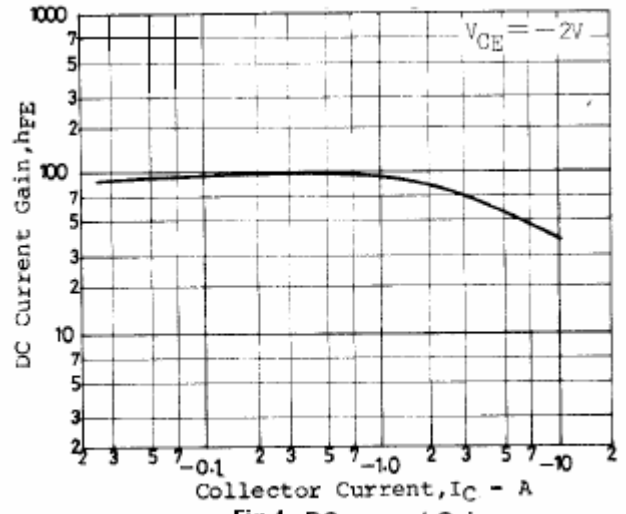


Fig.4 DC current Gain

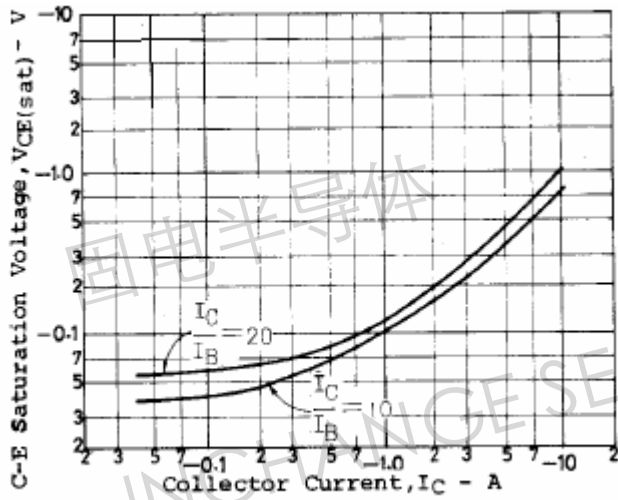


Fig.5 Collector-Emmitter Saturation Voltage

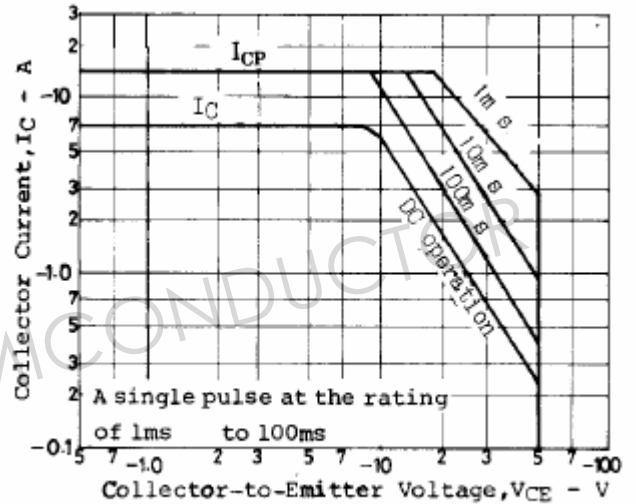


Fig.6 Safe Operating Area